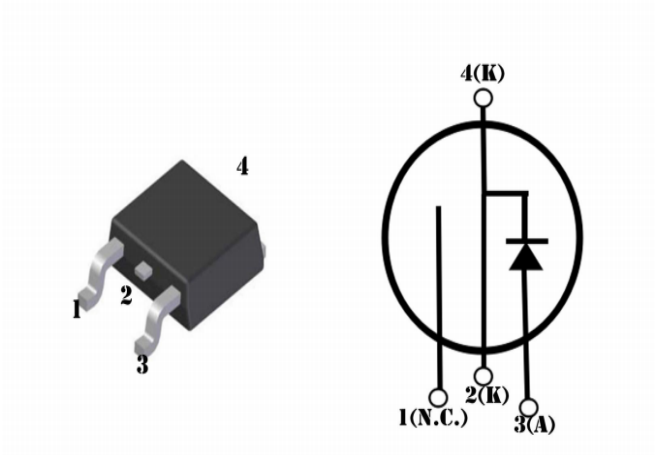
SiC Schottky Barrier Diode

CI10S120D

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

Package



Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters

Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_R	DC Peak Reverse Voltage	1200	V		
I_F	Continuous Forward Current	45 23 10	A	T_C=25°C T_C=135°C T_C=162°C	Fig. 3
I_{FRM}	Repetitive Peak Forward Surge Current	65 39.5	A	T_C=25°C, t_P=10 ms, Half Sine Pulse T_C=110°C, t_P=10 ms, Half Sine Pulse	
I_{FSM}	Non-Repetitive Forward Surge Current	79 65	A	T_C=25°C, t_P=10 ms, Half Sine Pulse T_C=110°C, t_P=10 ms, Half Sine Pulse	Fig. 8
$I_{F,Max}$	Non-Repetitive Peak Forward Current	760 630	A	T_C=25°C, t_P=10 μs, Pulse T_C=110°C, t_P=10 μs, Pulse	Fig. 8
P_{tot}	Power Dissipation	175 90	W	T_C=25°C T_C=110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V_R=0-960V	
$\int i^2dt$	i^2t value	25 17.5	A^2s	T_C=25°C, t_P=10 ms T_C=110°C, t_P=10 ms	
T_J	Operating Junction Range	-55 to +175	°C		
T_{stg}	Storage Temperature Range	-55 to +135	°C		
	TO-252 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.0	1.6 2.8	V	I_F = 10 A T_J=25°C I_F = 10 A T_J=175°C	Fig. 1
I_R	Reverse Current	30 55	180 280	μA	V_R = 1200 V T_J=25°C V_R = 1200 V T_J=175°C	Fig. 2
Q_C	Total Capacitive Charge	50		nC	V_R = 800 V, I_F = 10A d*i*/d*t* = 200 A/μs T_J = 25°C	Fig. 5
C	Total Capacitance	757 46 39		pF	V_R = 0 V, T_J = 25°C, f = 1 MHz V_R = 400 V, T_J = 25°C, f = 1 MHz V_R = 800 V, T_J = 25°C, f = 1 MHz	Fig. 6
E_C	Capacitance Stored Energy	14.5		μJ	V_R = 800 V	Fig. 7

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.9	°C/W	Fig. 9

Typical Performance

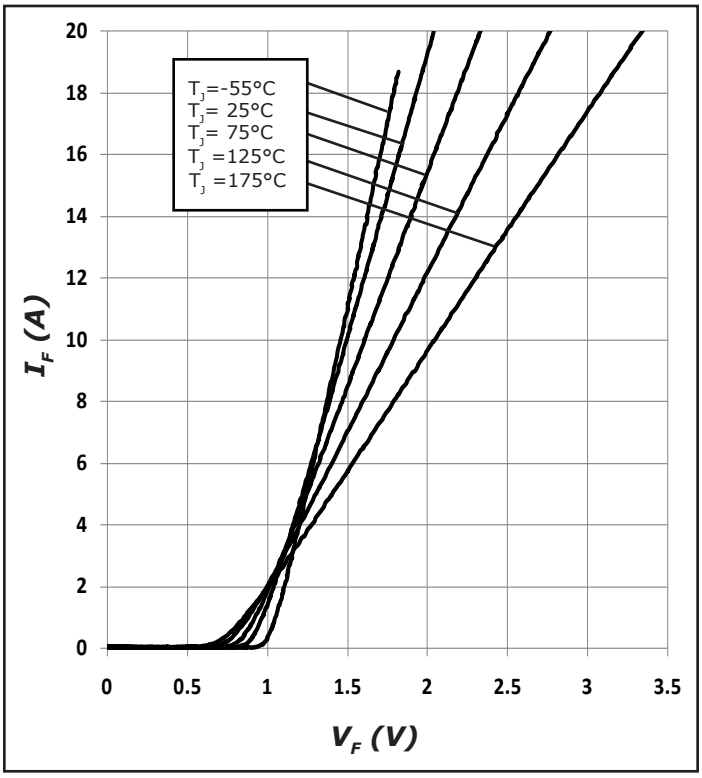


Figure 1. Forward Characteristics

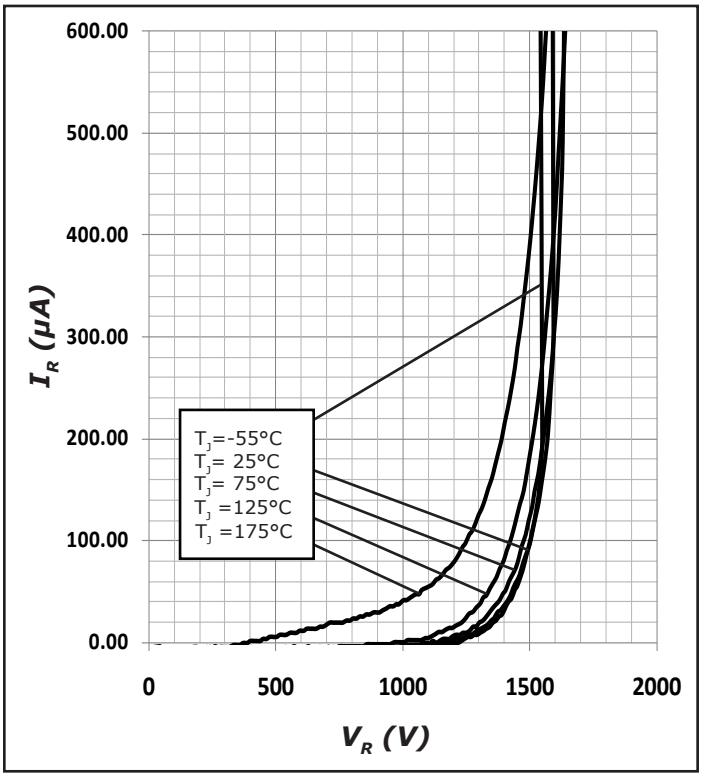


Figure 2. Reverse Characteristics

Typical Performance

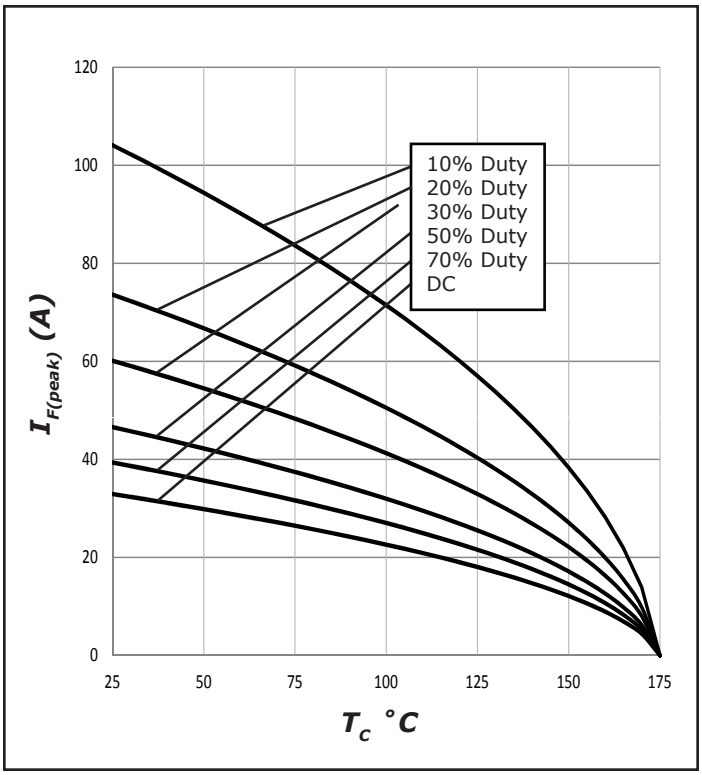


Figure 3. Current Derating

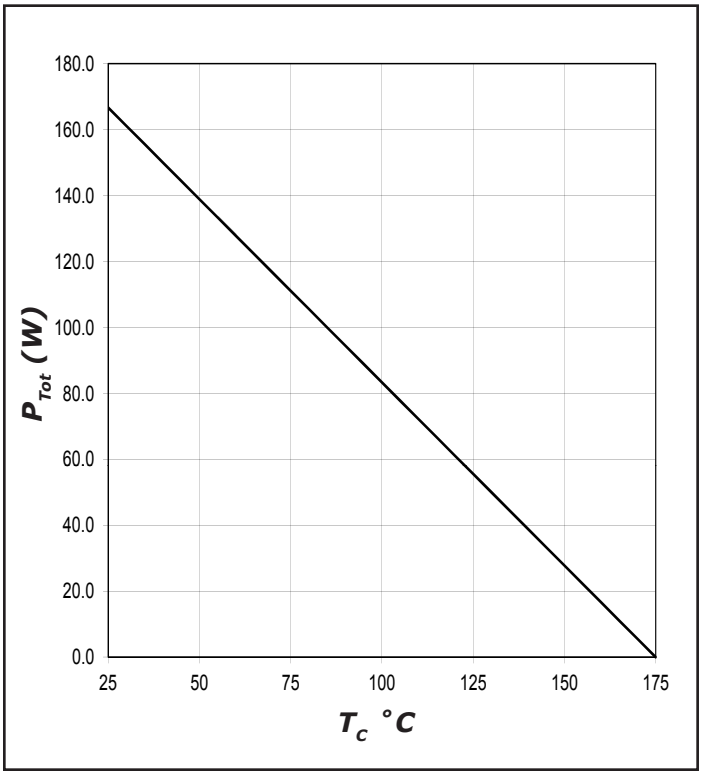


Figure 4. Power Derating

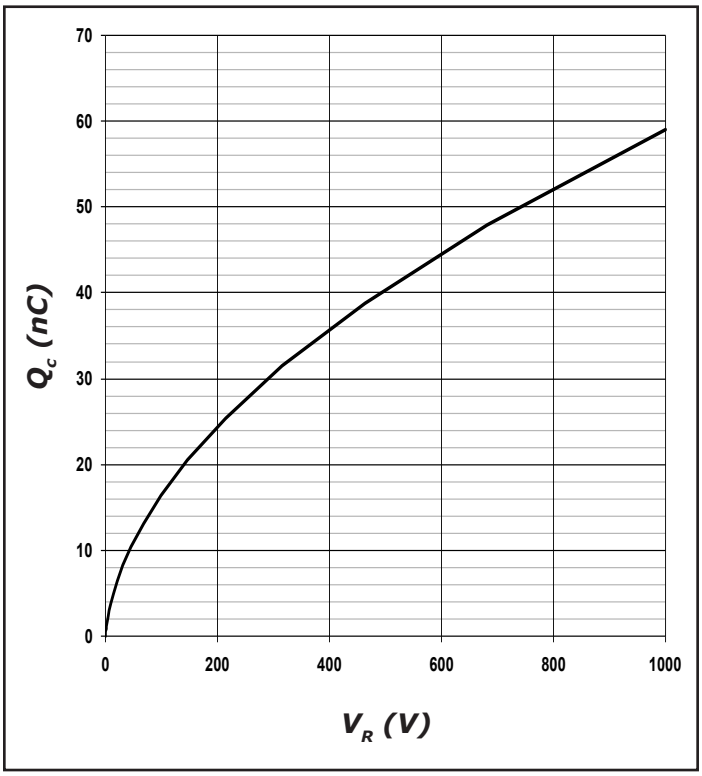


Figure 5. Recovery Charge vs. Reverse Voltage

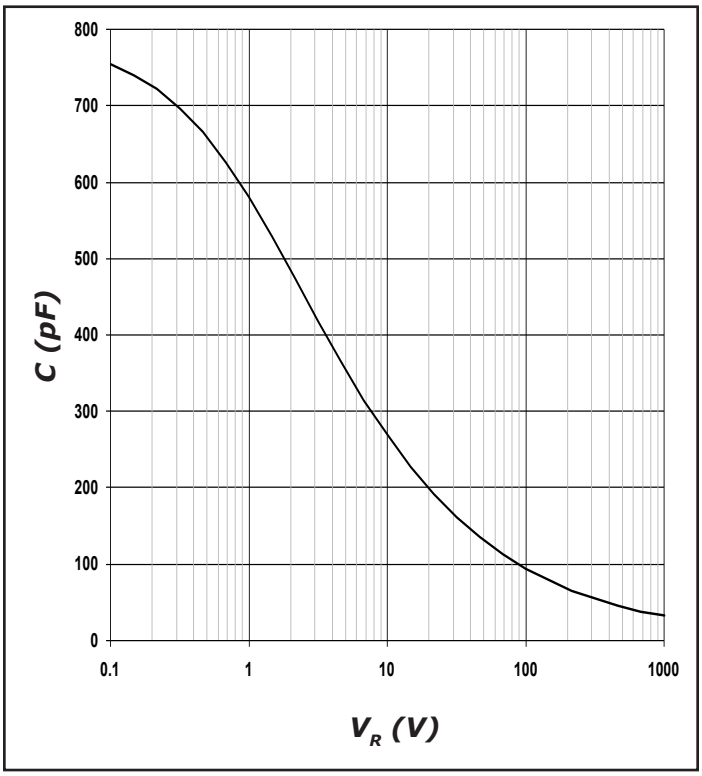


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

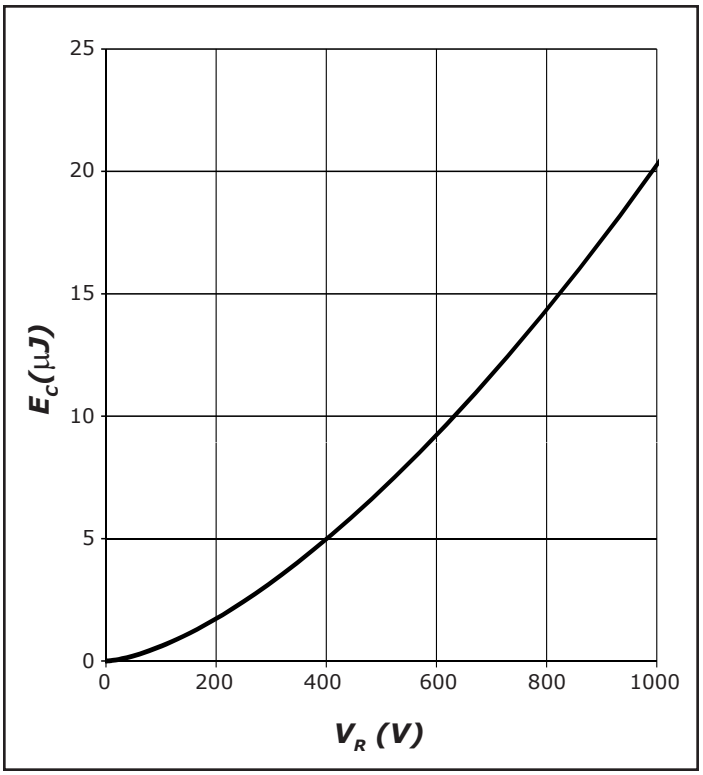


Figure 7. Typical Capacitance Stored Energy

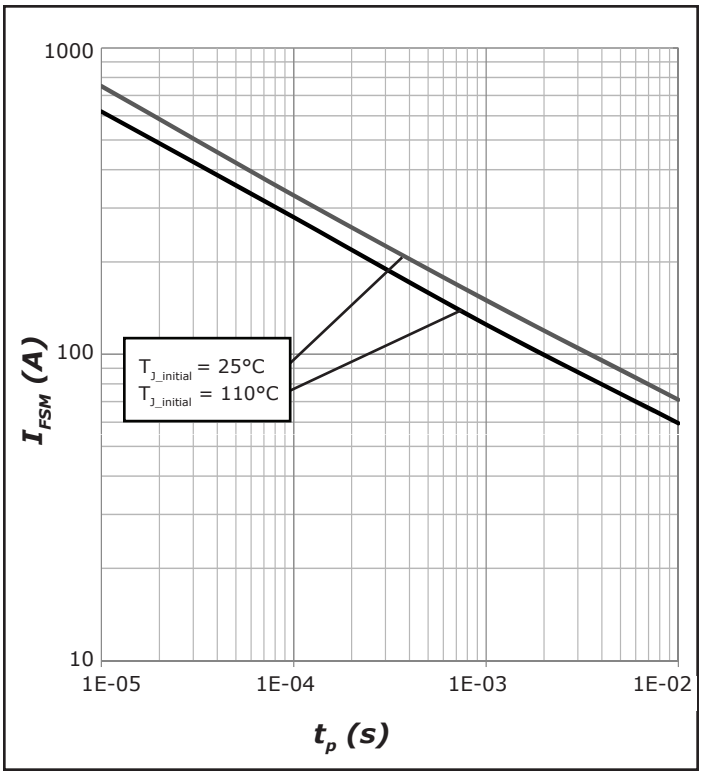


Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

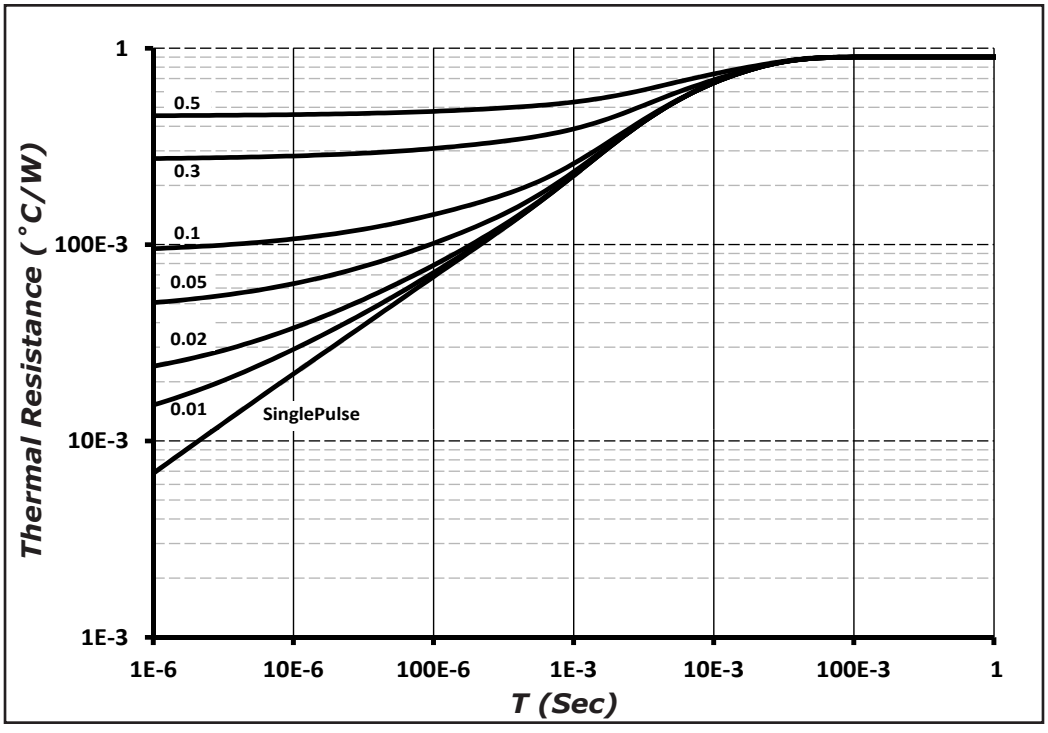
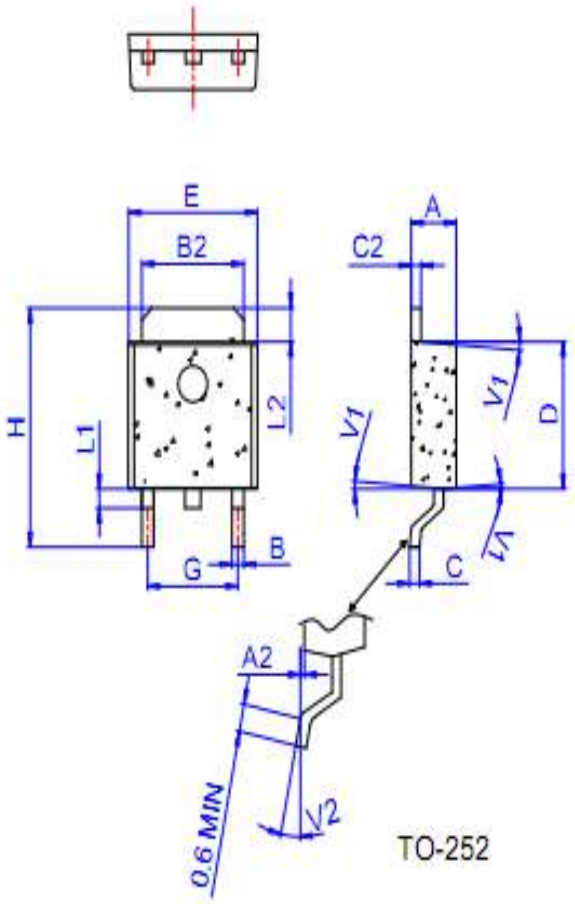


Figure 9. Transient Thermal Impedance

Package Dimensions



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°